TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

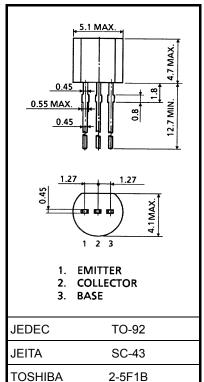
2SC3279

Strobe Flash Applications Medium Power Amplifier Applications

- High DC current gain and excellent hFE linearity
 : hFE (1) = 140~600 (VCE = 1 V, IC = 0.5 A)
 : hFE (2) = 70 (min), 200 (typ.) (VCE = 1 V, IC = 2 A)
- Low saturation voltage: V_{CE} (sat) = 0.5 V (max) (I_C = 2 A, I_B = 50 mA)

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|-----------------------------|--------------------|------------------|---------|------|--|
| Collector-base voltage | | V _{CBO} | 30 | V | |
| Collector-emitter voltage | | V _{CES} | 30 | V | |
| | | V _{CEO} | 10 | | |
| Emitter-base voltage | | V _{EBO} | 6 | V | |
| Collector current | DC | Ι _C | 2 | | |
| | Pulsed (Note 1) | I _{CP} | 5 | A | |
| Base current | | Ι _Β | 0.2 | А | |
| Collector power dissipation | | PC | 750 | mW | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | -55~150 | °C | |



Weight: 0.21 g (typ.)

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width = 10 ms (max), duty cycle = 30% (max)

Electrical Characteristics (Ta = 25°C)

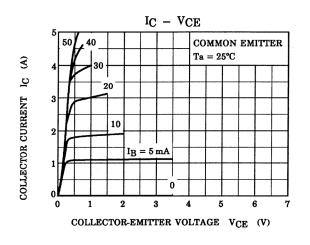
Note:

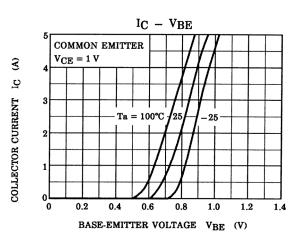
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|---------------------------------|---|-----|------|-----|------|
| Collector cut-off current | I _{CBO} | $V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0$ | _ | _ | 0.1 | μA |
| Emitter cut-off current | I _{EBO} | $V_{EB} = 6 V, I_C = 0$ | _ | _ | 0.1 | μA |
| Collector-emitter breakdown voltage | V (BR) CEO | $I_{C} = 10 \text{ mA}, I_{B} = 0$ | 10 | _ | | V |
| Emitter-base breakdown voltage | V _{(BR) EBO} | $I_E = 1 \text{ mA}, I_C = 0$ | 6 | _ | _ | V |
| DC current gain | h _{FE (1)} (Note 2) | $V_{CE} = 1 \text{ V}, \text{ I}_{C} = 0.5 \text{ A}$ | 140 | | 600 | |
| | h _{FE (2)} | $V_{CE} = 1 \text{ V}, I_{C} = 2 \text{ A}$ | 70 | 200 | | |
| Collector-emitter saturation voltage | V _{CE (sat)} | $I_{C} = 2 \text{ A}, I_{B} = 50 \text{ mA}$ | _ | 0.2 | 0.5 | V |
| Base-emitter voltage | V _{BE} | $V_{CE} = 1 V$, $I_C = 2 A$ | _ | 0.86 | 1.5 | V |
| Transition frequency | f _T | $V_{CE} = 1 \text{ V}, I_{C} = 0.5 \text{ A}$ | _ | 150 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ | _ | 27 | _ | pF |

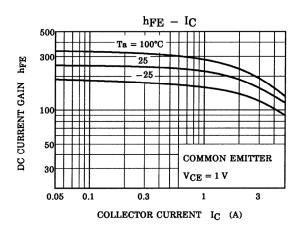
Note 2: hFE (1) classification L: 140~240, M: 200~330, N: 300~450, P: 420~600

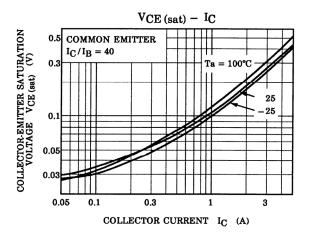
Unit: mm

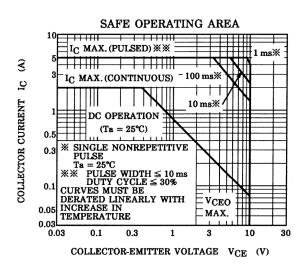
TOSHIBA

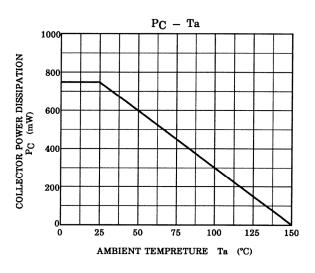












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20070701-EN GENERAL

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